RECTRON
SEMICONDUCTOR
TECHNICAL SPECIFICATION

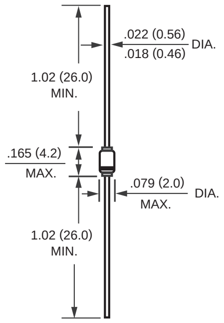
BAT86

SILICON PLANAR SCHOTTKY BARRIER DIODE

FEATURES

- Fast Switching Device(T_{RR}<4.0nS)
- DO-34 Package (JEDEC)
- Through-Hole Device Type Mounting
- Hermetically Sealed Glass
- Compression Bonded Construction
- All external surfaces are corrosion resistant and leads are readily solderable

DO-34



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

MAXIMUM RATINGES (@ T_A = 25°C unless otherwise noted)

RATINGS	SYMBOL	BAT86	UNITS
Maximum Forward Comtinuous Reverse Voltage	V_R	50	V
Maximum Forward Comtinuous Current @ T_A=25°C	I_F	200	mAmps
Repetitive Peak Forward Current tp≤1s:δ≤0.5	I_{FRM}	500	AmpsR
Surge Forward Current @ tp≤10ms	I_{FSM}	5	mAmps
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{STG}	-65 to + 150	°C

ELECTRICAL CHARACTERISTICS (@ T_A = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Reverse breakdown voltage (I_R=10µA)	$V_{(BR)R}$	50	-	-	V
Reverse voltage leakage current (V_R=40V)	I_R	-	-	5.0	µA
Forward voltage Pulse Tesx tp<300µs,δ<2% (I_F=0.1mA) (I_F=1mA) (I_F=10mA) (I_F=30mA) (I_F=100mA)	V_F	-	- - - - -	0.30 0.38 0.45 0.60 0.90	V
Diode capacitance (V_R=1,f=1MHz)	C_D	-	-	8.0	pF
Reveres recovery time (I_F=I_R=10mA,RL=100Ω,I_R=1mA)	t_{rr}	-	-	4.0	nS

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